

TECHNISCHE UNIVERSITÄT CHEMNITZ

Structural and electronic investigations of Bismuth multilayers

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orthorhombic structure



Experiments of Bi (110) on graphene

- Bismuth (110) growth on graphene on Si substrate
- Different numbers of multilayers found (> 3)
- Lattice constants from diffraction pattern:

Graphene: hexagonal $a_{
m Gr} = 2.43$ Å Bismuth: monoclinic $a_1 = 4.32$ Å , $a_2 = 4.61$ Å , $\alpha = 92.29^{\circ}$

Scanning tunneling microscopy (STM) images:



Structure model:







Bulk Bi bandstructure:

- Density functional theory (DFT)
- Software: Abinit
- Plane wave basis
- Exchange-correlation functional: GGA-PBE
- Pseudopotential: Hartwigsen-Goedecker-Hutter (HGH)
- Electron configuration of ₈₃Bi: [He] 4f¹⁴ 5d¹⁰ 6s² 6p³
- 5 valence electrons: 6s² 6p³
- Spin + spin-orbit coupling (SOC) included
- Energy cutoff: 20 Ha
- K point grid: $8^d \dots 16^d$ ($d \dots$ dimension)



 Charge transferred from Bi to graphene

Density of states:

- HOMO peaks fit experiment
- LUMO peak fit better for 1 ML graphene
- Bandgap missing



Structure calculations: even/odd effects, but no black phosphorus lattice Bandstructure: charge transferred from Bi to graphene Density of states: HOMO/LUMO peaks fit, bandgap missing



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